

BAT54 / A / C / S

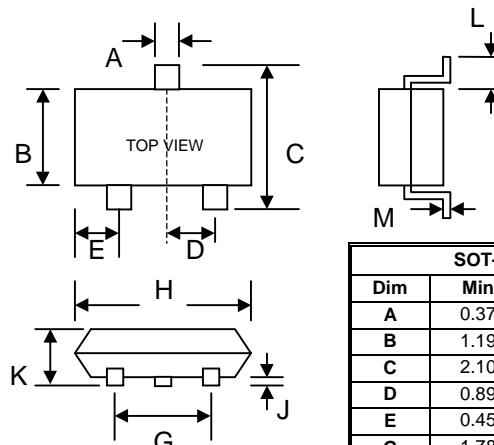
SURFACE MOUNT SCHOTTKY BARRIER DIODE

Features

- Low Turn-on Voltage
- Fast Switching
- PN Junction Guard Ring for Transient and ESD Protection
- Designed for Surface Mount Application
- Plastic Material – UL Recognition Flammability Classification 94V-O

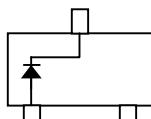
Mechanical Data

- Case: SOT-23, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: See Diagrams Below
- Weight: 0.008 grams (approx.)
- Mounting Position: Any

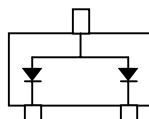


SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.19	1.40
C	2.10	2.50
D	0.89	1.05
E	0.45	0.61
G	1.78	2.05
H	2.65	3.05
J	0.013	0.15
K	0.89	1.10
L	0.45	0.61
M	0.076	0.178

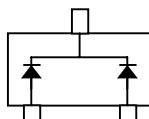
All Dimensions in mm



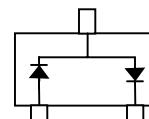
TOP VIEW
BAT54



TOP VIEW
BAT54A



TOP VIEW
BAT54C



TOP VIEW
BAT54S

Maximum Ratings and Electrical Characteristics, Single Diode @ $T_A=25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}		
Working Peak Reverse Voltage	V_{RWM}	30	V
DC Blocking Voltage	V_R		
Average Rectified Output Current	I_O	100	mA
Forward Continuous Current (Note 1)	I_F	200	mA
Repetitive Peak Forward Current (Note 1)	I_{FRM}	300	mA
Forward Surge Current @ $t_p < 1.0\text{s}$ (Note 1)	I_{FSM}	600	mA
Power Dissipation (Note 1)	P_d	200	mW
Typical Thermal Resistance, Junction to Ambient Air	$R_{\theta JA}$	500	K/W
Operating and Storage Temperature Range	T_j, T_{STG}	-65 to +125	°C

Note: 1. Device on fiberglass substrate.

Maximum Ratings and Electrical Characteristics, Single Diode @ $T_A=25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Breakdown Voltage	$V_{(\text{BR})R}$	30	—	—	V	$I_{RS} = 100\mu\text{A}$
Forward Voltage	V_F	—	—	240 320 400 500 1000	mV	$t_p < 300\mu\text{s}$, duty cycle <2% @ $I_F = 0.1\text{mA}$ @ $I_F = 1\text{mA}$ @ $I_F = 10\text{mA}$ @ $I_F = 30\text{mA}$ @ $I_F = 100\text{mA}$
Reverse Leakage Current	I_R	—	—	2.0	μA	$t_p < 300\mu\text{s}$, duty cycle <2% @ $V_R = 25\text{V}$
Junction Capacitance	C_j	—	—	10	pF	$V_R = 1.0\text{V}$, $f = 1.0\text{MHz}$
Reverse Recovery Time	t_{rr}	—	—	5.0	nS	$I_F = 10\text{mA}$ through $I_R = 10\text{mA}$ to $I_R = 1.0\text{mA}$, $R_L = 100\Omega$